

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 30	0.036 at V _{GS} = - 10 V	- 5.2		
	0.055 at V _{GS} = - 4.5 V	- 4.2		

FEATURES

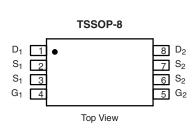
- Halogen-free
- TrenchFET® Power MOSFETs

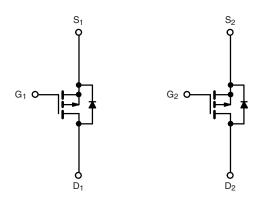


RoHS COMPLIANT

APPLICATIONS

- Load Switch
- · Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS TA	$_{A}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunin Courset /T 450 °C\2	T _A = 25 °C	- I _D	- 5.2	- 4.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.2	- 3.6	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.70	
Marina Barra Birainatina	T _A = 25 °C	- P _D	1.14	0.83	W
Maximum Power Dissipation ^a	T _A = 70 °C		0.73	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum landing to Audienta	t ≤ 10 s	- R _{thJA}	86	110		
Maximum Junction-to-Ambient ^a	Steady State		124	150	°C/W	
Maximum Junction-to-Foot	Steady State	R _{thJF}	52	65		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



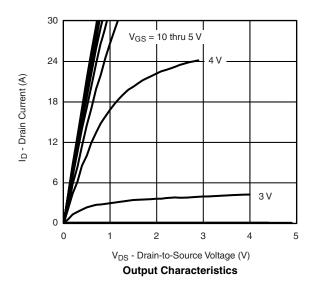
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	= 0 V, V _{GS} = ± 20 V		± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$				μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
Drain-Source On-State Resistance ^a	В	$V_{GS} = -10 \text{ V}, I_D = -4.7 \text{ A}$		0.036		Ω	
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3.8 \text{ A}$		0.055			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.7 A		14		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.74	- 1.1	V	
Dynamic ^b	•		•	·!			
Total Gate Charge	Q_g			13	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC	
Gate-Drain Charge	Q_{gd}			5.8		1	
Gate Resistance	R_{g}	f = 1.0 MHz		4.6		Ω	
Turn-On Delay Time	t _{d(on)}			13	20		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_G=$ 6 Ω		52	80	ns	
Fall Time	t _f			26	40		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dl/dt = 100 A/μs		40	60		

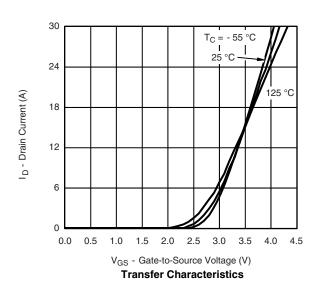
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

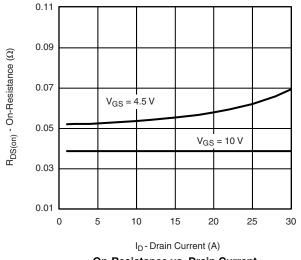
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

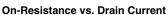


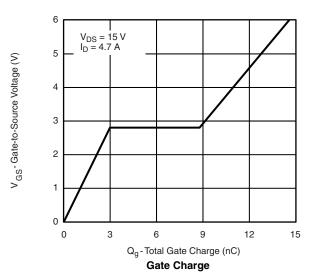


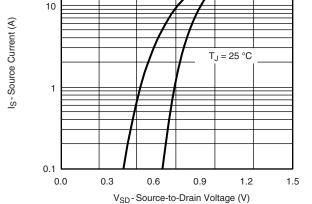


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









Source-Drain Diode Forward Voltage

T_J = 150 °C

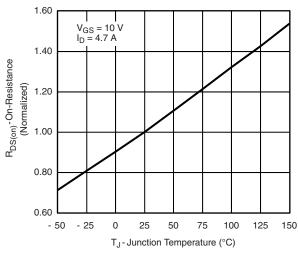
30

C-Capacitance (pF) 1200 $\mathsf{C}_{\mathsf{iss}}$ 800 $\mathsf{C}_{\mathsf{oss}}$ 400 0 0 5 10 15 20 25 30 V_{DS} -Drain-to-Source Voltage (V)

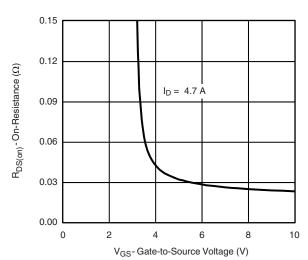
2000

1600

Capacitance



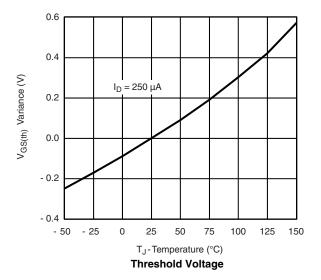
On-Resistance vs. Junction Temperature

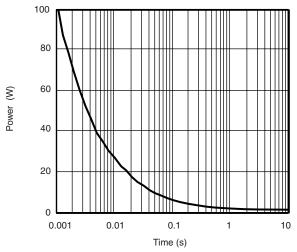


On-Resistance vs. Gate-to-Source Voltage

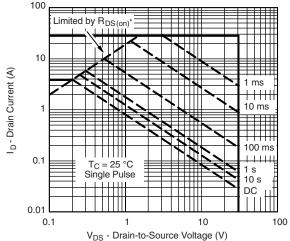


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

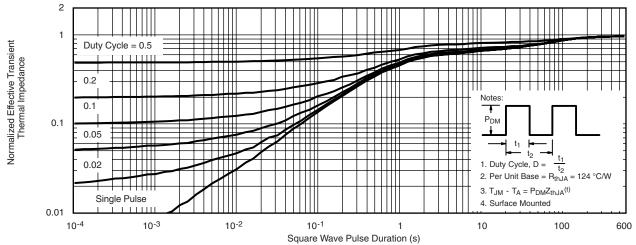




Single Pulse Power, Junction-to-Ambient



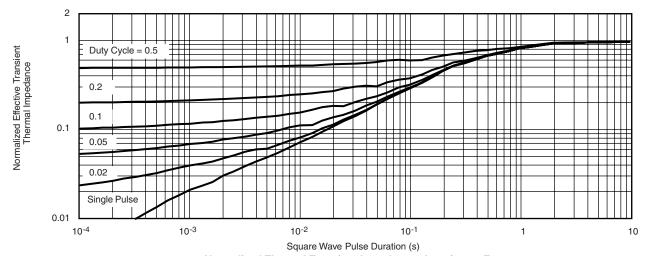
 * V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified **Safe Operating Area, Junction-to-Case**



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot



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